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## (54) APPARATUS AND METHOD FOR TREATING UNDER HIGH PRESSURE

## (57)Abstract:

PROBLEM TO BE SOLVED: To provide an apparatus and a method for treating a substrate under high pressure, in which the substrate can be treated by using a pure processing fluid so that the atmospheric component intruded into a treating tank when the substrate is placed is not made to flow in a fluid producing/recovering system.

SOLUTION: Valves V1, V2, V3, V4 and V6 are closed and only a valve V5 is opened when the door of a substrate cleaning tank 5 is opened for placing the substrate so that gaseous carbon dioxide is supplied to the tank 5 and the tank 5 is purged for preventing the atmospheric component from intruding into the tank 5. Next, the door of the tank 5 is closed and the valve V6 is opened at the same time to form a venting line of the tank 5 so that the gas existing in the tank 5 and its surrounding pipes is pushed out to the atmosphere by the supplied gaseous carbon dioxide and the tank 5 is purged so that the atmospheric component to intrude into the tank 5 and its surrounding pipes by some rare accident does not stay behind. Then, the substrate is cleaned by using supercritical carbon dioxide.

